Attorney's Docket No.:06618-424002

Amendment to the Claims:

This listing of claims replaces all prior versions, and listings, of claims in the application:

(Currently Amended) A method of forming an 1. electrically active material, comprising:

obtaining a silicon substrate;

forming a first material on said silicon substrate; forming a conductive layer on said first material, said conductive layer formed of a electrically conductive, fully oxidized, transition metal material combined with a SiO2 which is immiscible with said electrically conductive material, and a ferroclectric-layer, -over-said-conducting layer- said conductive layer consisting essentially of three materials forming a ternary oxide material having first and second immiscible compounds, said first and second immiscible compounds having one common element, wherein said first compound is of the form TMOx where Tm is a transition metal that is one of Ru, Mo, Rh, Os, Re, W, Cr, Ti, In or Ir, and said second compound is of the form JOy where J is a different material than Tm and said first and second compounds being formed in an amorphous state, and being meta-stable relative to one another over a temperature range, and wherein said common element is oxygen;

directly connecting said ferroelectric layer to said other material without a barrier layer therebetween; and

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heating said device in a high temperature environment between 300 and 700 °C and oxidizing environment without forming substantial oxidization in said first material.

- (Currently Amended) A method as in claim 1, wherein 2, said first material is a dielectric material.
- (Original) A device as in claim 1, wherein said electrical material is formed by sputtering an oxygen containing gas at least one target containing distinct sites of Ruthenium and silicon.

Kindly add the following new claim:

4. (New) A method as in claim 1, wherein the transition metal is an amorphous combination of ruthenium dioxide and silicon dioxide